

FP103

DC/DC Converter Applications

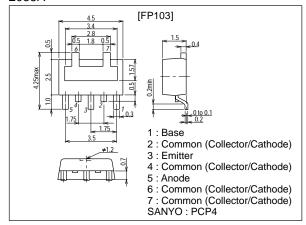
Features

- Composite type with a PNP transistor and a Shottky barrier diode contained in one package, facilitating high-density mounting.
- The FP103 is formed with 2chips, one being equivalent to the 2SB1121 and the other the SB07-03C, placed in one package.

Package Dimensions

unit:mm

2088A



Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
[TR]	'		'	
Collector-to-Base Voltage	V _{CBO}		-30	V
Collector-to-Emitter Voltage	VCEO		-25	V
Emitter-to-Base Voltage	V _{EBO}		-6	V
Collector Current	IC		-2	Α
Collector Current (Pulse)	ICP		-5	Α
Base Current	IB		-400	mA
Collector Dissipation	PC		1.3	W
Junction Temperature	Tj	Mounted on a ceramic board (250mm²×0.8mm)	150	°C
Strage Temperature	Tstg		-55 to +150	°C
[SBD]	•			
Repetitive Peak Reverse Voltage	V _{RRM}		30	V
Non-repetitive Peak Reverse Surge Voltage	V _{RSM}		35	V
Average Rectified Current	Io		700	mA
Surge Forward Current	IFSM	50Hz sine wave, 1cycle	5	Α
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

Marking:103

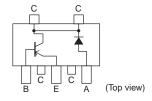
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Electrical Characteristics at Ta = 25°C

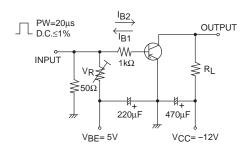
.Parameter	Symbol	Conditons		Ratings		
	Symbol		min	typ	max	Unit
[TR]	•		•			
Collector Cutoff Current	I _{CBO}	V _{CB} =-20V, I _E =0			-0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC Current Gain	h _{FE} 1	V _{CE} =-2V, I _C =-100mA	140		560	
	h _{FE} 2	V _{CE} =-2V, I _C =-1.5A	65			
Gain-Bandwidth Product	fT	V _{CE} =-10V, I _C =-50mA		150		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		32		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-1.5A, I _B =-75mA		-0.35	-0.6	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-1.5A, I _B =-75mA		-0.85	-1.2	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =-10μA, I _E =0	-30			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =−1mA, R _{BE} =∞	-25			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, IC=0	-6			V
Turn-ON Time	t _{on}	See specified Test Circuit		60		ns
Storage Time	tstg	See specified Test Circuit		350		ns
Fall Time	t _f	See specified Test Circuit		25		ns
[SBD]	•		•			
Reverse Voltage	VR	I _R =300μA	30			V
Forward Voltage	٧ _F	I _F =700mA			0.55	V
Reverse Current	I _R	V _R =15V			80	μΑ
Interterminal Capacitance	С	V _R =10V, f=1MHz		28		pF
Reverse Recovery Time	t _{rr}	I _F =I _R =100mA, See specified Test Circuit			10	ns
Thermal Resistance	Rthj-a	Mounted on a ceramic board (250mm ² ×0.8mm)		120		

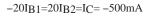
Electrical Connection

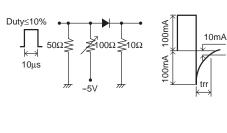


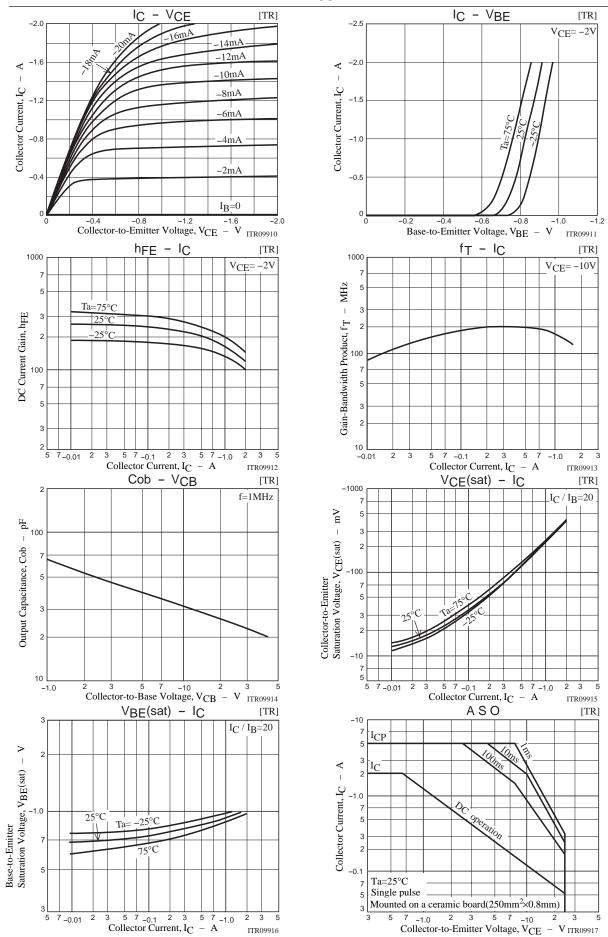
Switching Time Test Circuit

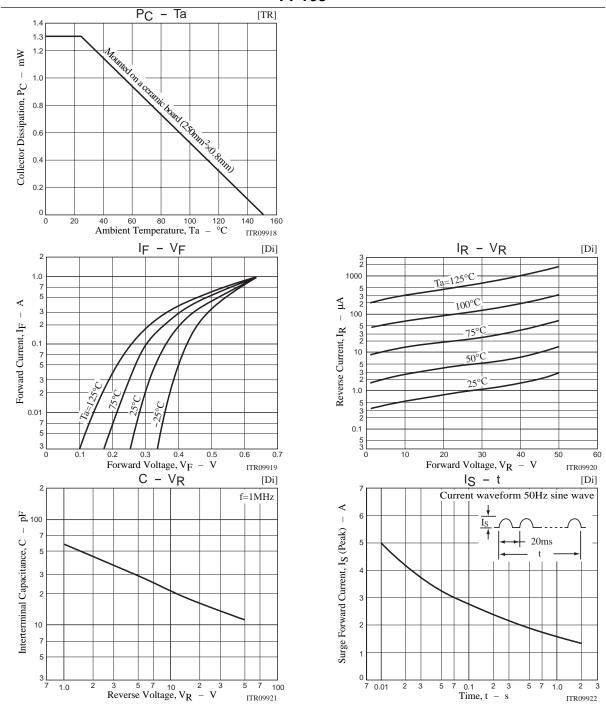
[TR] [SBD]











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